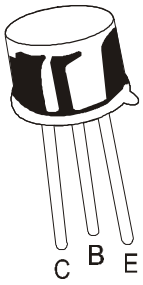
PNP SILICON PLANAR EPITAXIAL TRANSISTOR

CSA537

TO-39
Metal Can Package



MEDIUM SPEED SWITCHING AND LINEAR AMPLIFIER APPLICATIONS

ABSOLUTE MAXIMUM RATINGS (Ta=25ºC unless specified otherwise)

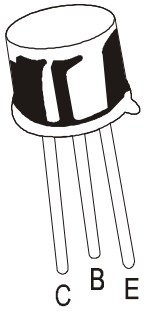
DESCRIPTION	SYMBOL	VALUE	UNITS
Collector Emitter Voltage	V_{CEO}	50	V
Collector Base Voltage	V_{CBO}	60	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current Continuous	I_C	0.7	A
Emitter Current Contiuuous	I_E	0.7	A
Power Dissipation	P_D	0.75	W
Junction Temperature	T_j	200	ºC
Storage Temperature	T_{stg}	-55 To +200	ºC

ELECTRICAL CHARACTERISTICS (Ta=25ºC unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	VALUE	UNITS
Collector Base Breakdown Voltage	B_{VCBO}	I_C=10µA, I_E= 0	>60	V
Collector Emitter Breakdown Voltage	B_{VCEO}	I_C=5mA, I_E=0	>50	V
Emitter Base Breakdown Voltage	BV_{EBO}	I_E=10mA, I_C=0	>5	V
Collector Cutoff Current	I_{CBO}	V_{CB}=30V, I_E=0	<50	nA
Emitter Cutoff Current	I_{EBO}	V_{EB}=3V, I_C=0	<50	nA
Collector Emitter(Sat) Voltage	$V_{CE(Sat)}$	I_C=150mA,I_B=15mA	<0.5	V
Base Emitter (Sat) Voltage	$V_{BE(Sat)}$	I_C=150mA,I_B=15mA	<1.1	V
DC Current Gain	$h_{FE\ (1)}$	I_C=50mA,V_{CE}=4V	50-160	
	$h_{FE\ (2)}$	I_C=400mA,V_{CE}=4V	>20	
Small Signal Current Gain	$\lvert h_{fe} \rvert$	I_C=20mA, V_{CE}=10V,	>1.0	V
		f=100MHz		V
Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz	<35	pF

NPN HIGH VOLTAGE SILICON TRANSISTORS

CSA537



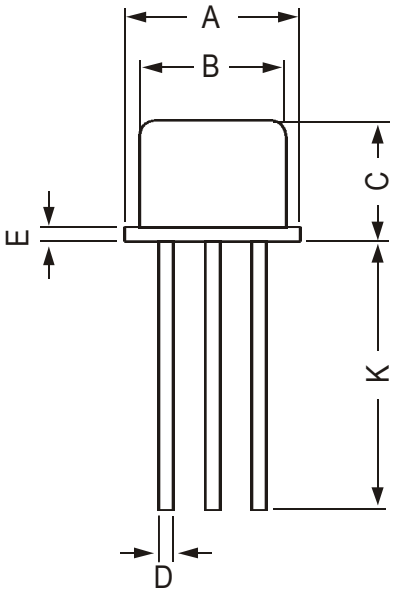
TO-39
Metal Can Package

ELECTRICAL CHARACTERISTICS (Ta=25ºC unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	VALUE	UNITS
SWITCHING CHARACTERISTICS				
Turn on Time	t_{on}	V_{CC}=6.5V, I_C=150mA,	<50	ns
		I_{B1}=15mA, I_{B2} =0		
Turn off Time	t_{off}	V_{CC}=6.5V, I_C=150mA,	<350	ns
		I_{B1}=I_{B2} =15mA		
Storage Time	t_{stg}	V_{CC}=6.5V, I_C=150mA,	<300	ns
		I_{B1}=I_{B2} =15mA		

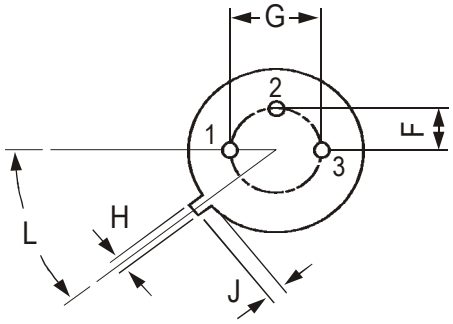
CLASSIFICATION	**B**	**C**
$h_{FE\ (1)}$	**500-100**	**80-160**

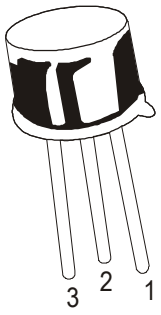
TO-39 Metal Can Package



All dimensions are in mm

DIM	MIN	MAX
A	8.50	9.39
B	7.74	8.50
C	6.09	6.60
D	0.40	0.53
E	—	0.88
F	2.41	2.66
G	4.82	5.33
H	0.71	0.86
J	0.73	1.02
K	12.70	—
L	42 DEG	48 DEG





PIN CONFIGURATION
1. EMITTER
2. BASE
3. COLLECTOR

Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	**Net Weight/Qty**	**Size**	**Qty**	**Size**	**Qty**	**Gr Wt**
TO-39	**500 pcs/polybag**	**540 gm/500 pcs**	**3" x 7.5" x 7.5"**	**20K**	**17" x 15" x 13.5"**	**32K**	**40 kgs**

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